

Title (en)

LOW TEMPERATURE FORMATION OF BACKSIDE OHMIC CONTACTS FOR VERTICAL DEVICES

Title (de)

HERSTELLUNG VON OHMSCHEN RÜCKSEITENKONTAKTEN ZU VERTIKAL ANGEORDNETEN HALBLEITERVORRICHTUNGEN BEI NIEDRIGER TEMPERATUR

Title (fr)

FORMATION A BASSE TEMPERATURE DE CONTACTS OHMIQUES REALISES SUR L'ENVERS DESTINES A DES DISPOSITIFS VERTICAUX

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Application

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Abstract (en)

[origin: WO0016382A1] The invention comprises a method for forming a metal-semiconductor ohmic contact (18) for use in a semiconductor device (10) having a plurality of epitaxial layers (14a-c) wherein the ohmic contact (18) is preferably formed after deposition of the epitaxial layers (14a-c). The invention also comprises a semiconductor device comprising a plurality of epitaxial layers and an ohmic contact.

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